

Product Summary

BV_{DSS}	$R_{DS(ON)} \text{ max}$	I_D $T_A = +25^\circ\text{C}$
-50V	$10\Omega @ V_{GS} = -5V$	-130mA

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The BSS84Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

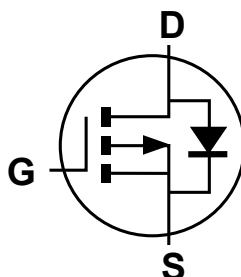
Mechanical Data

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)

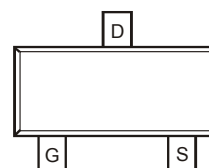
SOT23



Top View



Equivalent Circuit



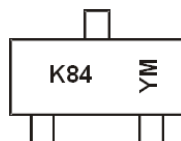
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
BSS84Q-7-F	SOT23	3000/Tape & Reel
BSS84Q-13-F	SOT23	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



K84 = Product Type Marking Code
 YM = Date Code Marking
 Y or $\bar{Y}$ = Year (ex: I = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	1998		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	J		I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Drain-Gate Voltage $R_{GS} \leq 20\text{k}\Omega$	V_{DGR}	-50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current (Note 5)	I_D	-130	mA
Pulsed Drain Current	I_{DM}	-1.2	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DS}	-50	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	$V_{DS} = -50\text{V}, V_{GS} = 0\text{V}, T_J = +25^\circ\text{C}$
		—	—	-2	μA	$V_{DS} = -50\text{V}, V_{GS} = 0\text{V}, T_J = +125^\circ\text{C}$
		—	—	-100	nA	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, T_J = +25^\circ\text{C}$
Gate-Body Leakage	I_{GSS}	—	—	± 10	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.8	—	-2.0	V	$V_{DS} = V_{GS}, I_D = -1\text{mA}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.2	10	Ω	$V_{GS} = -5\text{V}, I_D = -0.100\text{A}$
Forward Transconductance	g_{FS}	0.05	—	—	S	$V_{DS} = -25\text{V}, I_D = -0.1\text{A}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	24.6	45	pF	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	4.7	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.8	12	pF	
Gate Resistance	R_g	—	916	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	—	0.28	—	nC	$V_{DS} = -10\text{V}, I_D = -0.1\text{A}$
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g	—	0.59	—	nC	
Gate-Source Charge	Q_{gs}	—	0.09	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.08	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	10	—	ns	$V_{DD} = -30\text{V}, I_D = -0.27\text{A}, R_{GEN} = 50\Omega, V_{GS} = -10\text{V}$
Turn-Off Delay Time	$t_{D(OFF)}$	—	18	—	ns	

Notes: 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at <http://www.diodes.com/package-outlines.html>.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to production testing.

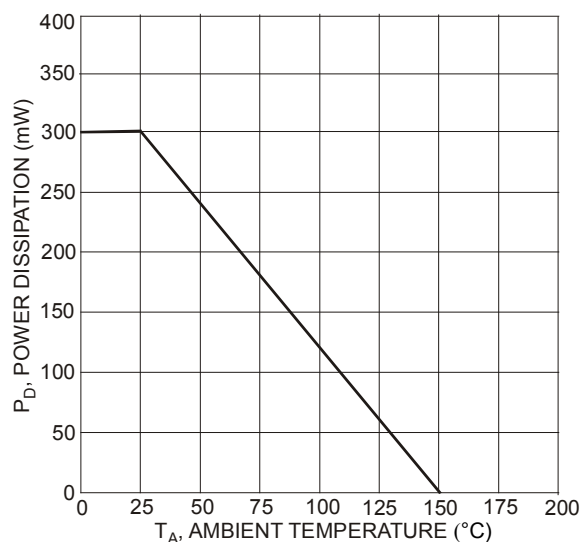


Fig. 1 Max Power Dissipation vs. Ambient Temperature

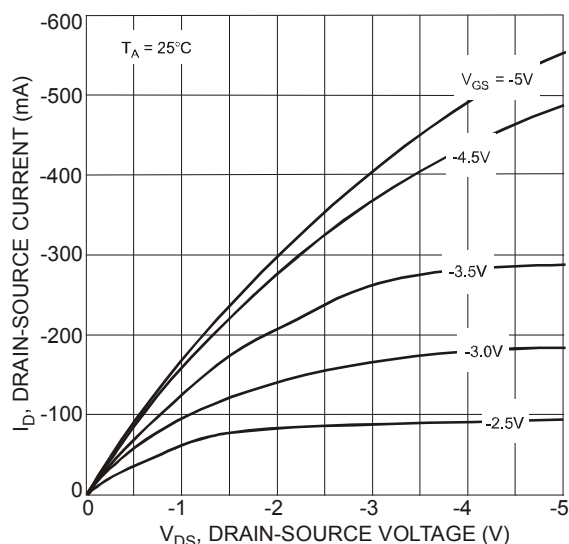


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

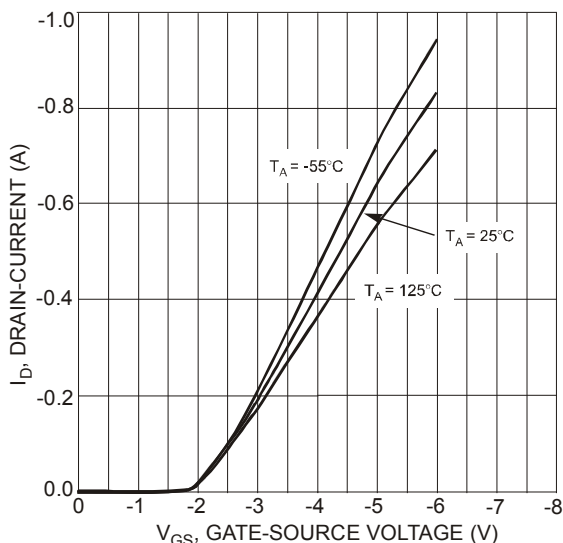


Fig. 3 Drain-Current vs. Gate-Source Voltage

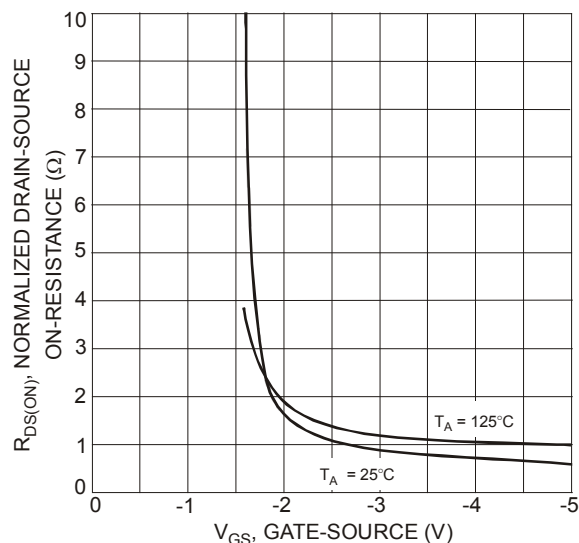


Fig. 4 On-Resistance vs. Gate-Source Voltage

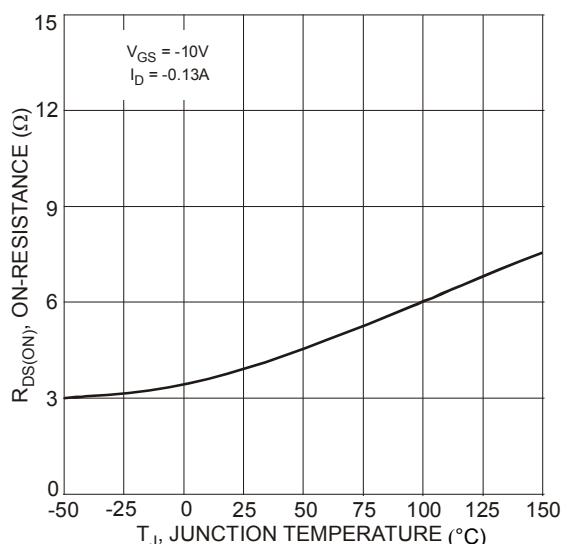


Fig. 5 On-Resistance vs. Junction Temperature

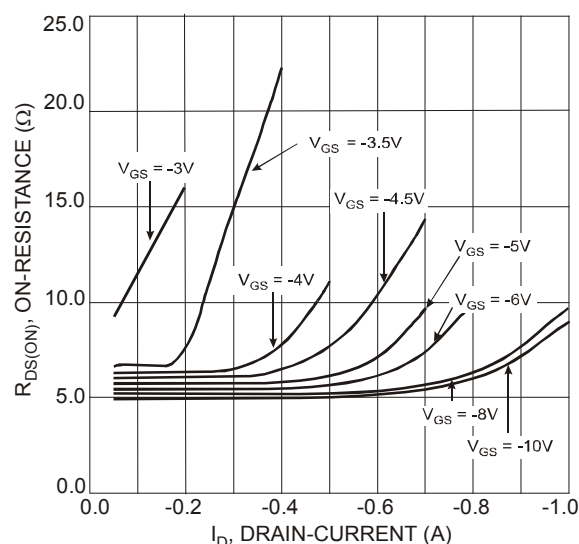


Fig. 6 On-Resistance vs. Drain-Current

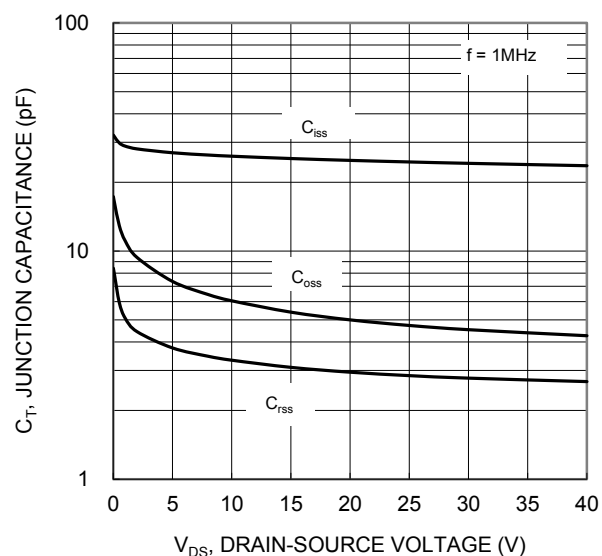


Fig. 7 Typical Junction Capacitance

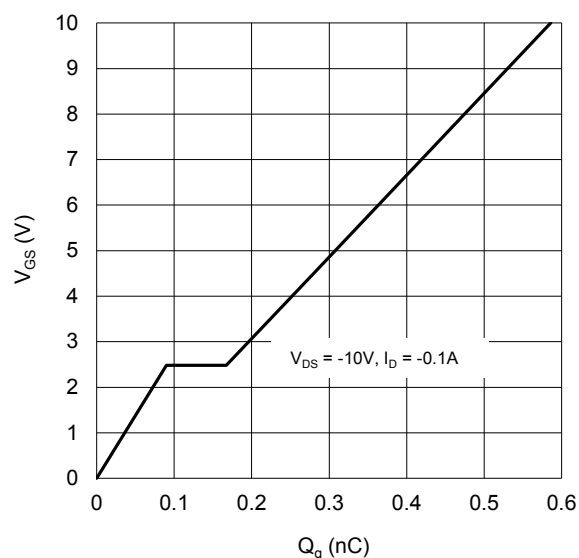


Fig. 8 Gate Charge

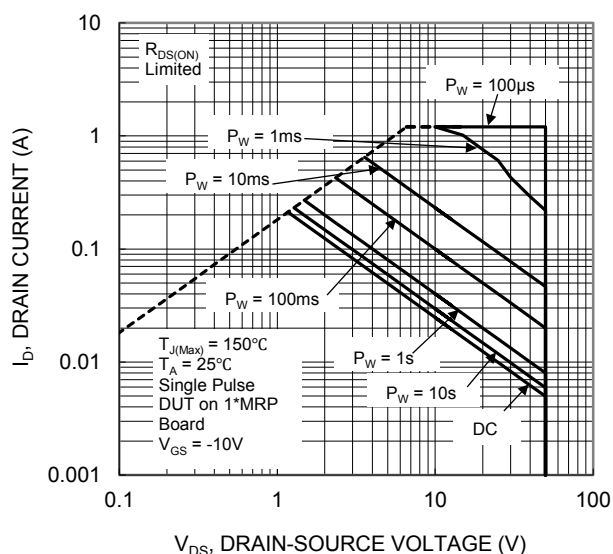
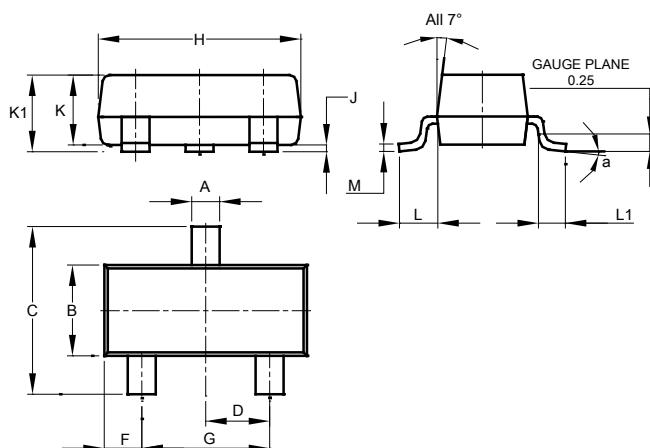


Fig. 9 SOA, Safe Operation Area

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

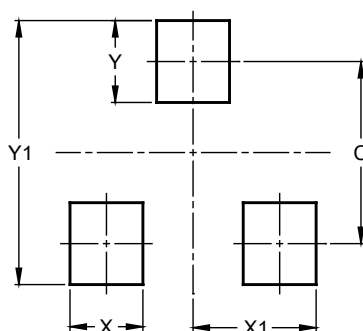


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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